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Erratum: "Work function tuning and improved gate dielectric reliability with multilayer graphene as a gate electrode for metal oxide semiconductor field effect device applications" [Appl. Phys. Lett. 100, 233506 (2012)]

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Important typographic error in the last paragraph of page 4, in the line "Ti-N has a bond length of about 1.57 Å and Ti and N have atomic diameters of 2.84 nm and 1.36 nm, respectively" is identified. In this line, Ti and N atomic diameters are written in **nanometers**, while the units should be in **Angstroms**. These changes in the units of atomic diameter would not affect the conclusions of the paper.[1]

The authors would like to tender an apology for the mistake.

[1] A. Misra, M. Waikar, A. Gour, H. Kalita, M. Khare, M. Aslam, and A. Kottantharayil, Appl. Phys. Lett. **100**, 233506 (2012).

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